450V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D T_A = +25°C
450V	50Ω @ V_{GS} = 10V	140mA

Description

This new generation trench MOSFET features a unique structure combining the benefits of low on-resistance and fast switching, making it ideal for high efficiency power management applications.

Applications

- Off-line Power Supply Start-up Circuitry

Features and Benefits

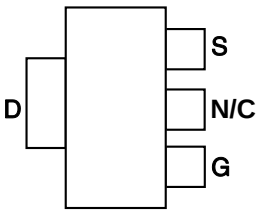
- High Voltage
- Low On-resistance
- Fast Switching Speed
- Low Gate Drive
- Low Threshold
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

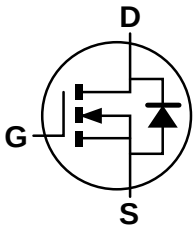
- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish (e3)
- Weight: 0.112 grams (Approximate)

SOT223

Top View



Pin Out - Top



Equivalent Circuit

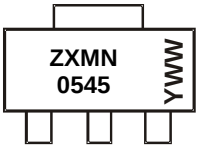
Ordering Information (Note 4)

Part Number	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXMN0545G4TA	ZXMN0545	7	12	1,000
ZXMN0545G4TC	ZXMN0545	13	12	4,000

Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information

SOT223



ZXMN0545 = Product Type Marking Code
YWW = Date Code Marking
Y or $\overline{Y}$ = Last Digit of Year (ex: 5 = 2015)
WW or $\overline{WW}$ = Week Code (01~53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	450	V
Gate-Source Voltage	V_{GSS}	±20	V
Continuous Drain Current (V_{GS} = 10V; T_A = +25°C) (Note 5)	I_D	140	mA
Pulsed Drain Current (Note 7)	I_{DM}	600	mA
Continuous Source Current (Body Diode) (Note 6)	I_S	140	mA
Pulsed Source Current (Body Diode) (Note 7)	I_{SM}	600	mA

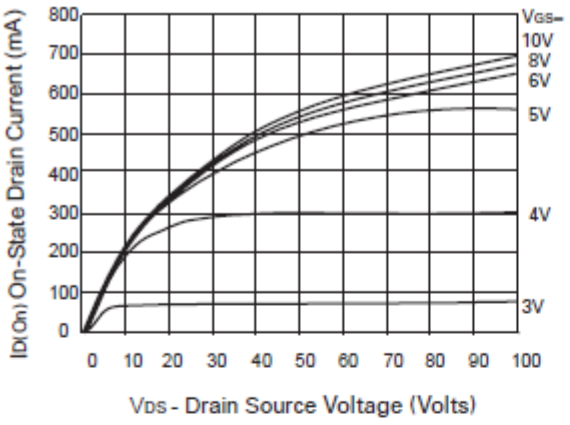
Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation at T_A = +25°C (Note 5) Linear Derating Factor	P_D	2.0 1.6	W mW/°C
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	62.5	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	32	°C/W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C

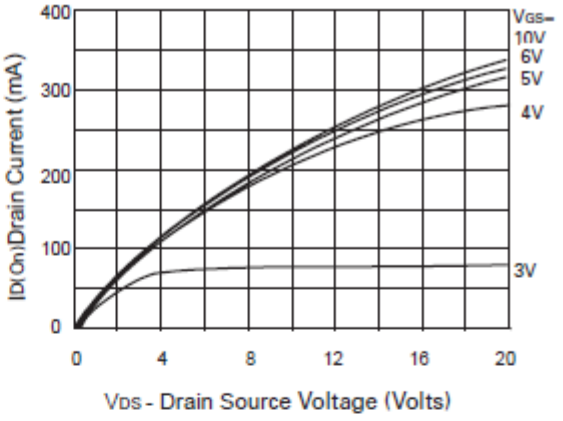
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	450	-	-	V	V_{GS} = 0V, I_D = 1mA
Zero Gate Voltage Drain Current	I_{DSS}	-	-	10 400	µA	V_{DS} = 450V, V_{GS} = 0V V_{DS} = 405V, V_{GS} = 0V, T = +125°C
Gate-Source Leakage	I_{GSS}	-	-	20	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	1	-	3	V	V_{DS} = V_{GS}, I_D = 1mA
Static Drain-Source On-Resistance (Note 8)	$R_{DS(ON)}$	-	-	50	Ω	V_{GS} = 10V, I_D = 100mA
Forward Transconductance (Notes 8 & 10)	g_{fs}	100	-	-	mS	V_{DS} = 25V, I_D = 100mA
On-State Drain Current (Note 8)	$I_{D(ON)}$	150	-	-	mA	V_{DS} = 25V, V_{GS} = 10V
DYNAMIC CHARACTERISTICS (Note 11)						
Input Capacitance (Note 10)	C_{iss}	-	-	70	pF	V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz
Output Capacitance (Note 10)	C_{oss}	-	-	10	pF	
Reverse Transfer Capacitance (Note 10)	C_{rss}	-	-	4	pF	
Turn-On Delay Time (Notes 9 & 10)	$t_{D(ON)}$	-	-	7	ns	V_{DD} = 25V, I_D = 100mA
Turn-On Rise Time (Notes 9 & 10)	t_R	-	-	7	ns	
Turn-Off Delay Time (Notes 9 & 10)	$t_{D(OFF)}$	-	-	16	ns	
Turn-Off Fall Time (Notes 9 & 10)	t_F	-	-	10	ns	

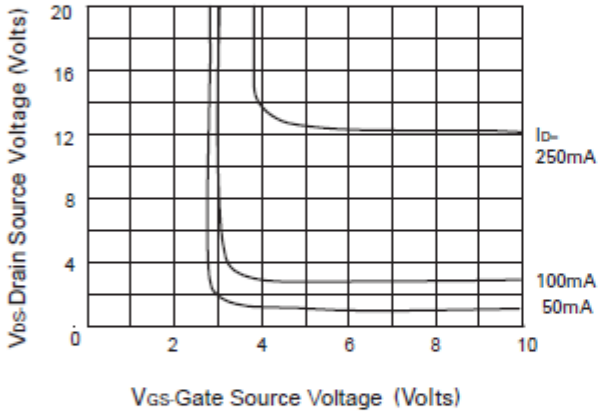
Notes:
5. For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.
6. For a device surface mounted on FR4 PCB measured at t ≤ 5 secs.
7. Repetitive rating - pulse width limited by maximum junction temperature. Refer to Transient Thermal Impedance graph.
8. Measured under pulsed conditions. Pulse width ≤ 300µs. Duty cycle ≤ 2%.
9. Switching characteristics are independent of operating junction temperature.
10. Sample test.
11. For design aid only, not subject to production testing.



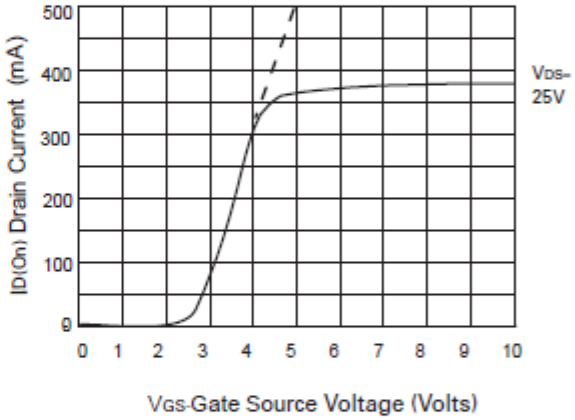
Output characteristics



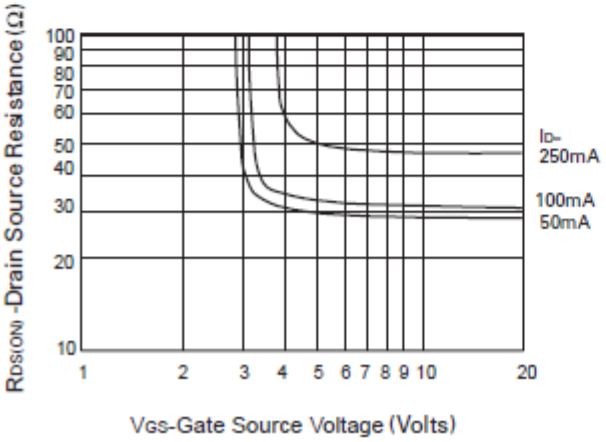
Saturation characteristics



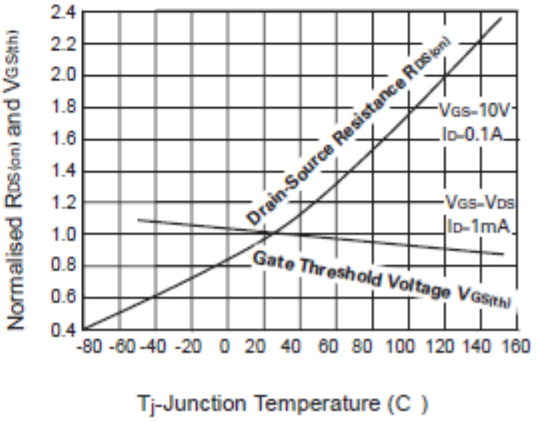
Voltage saturation characteristics



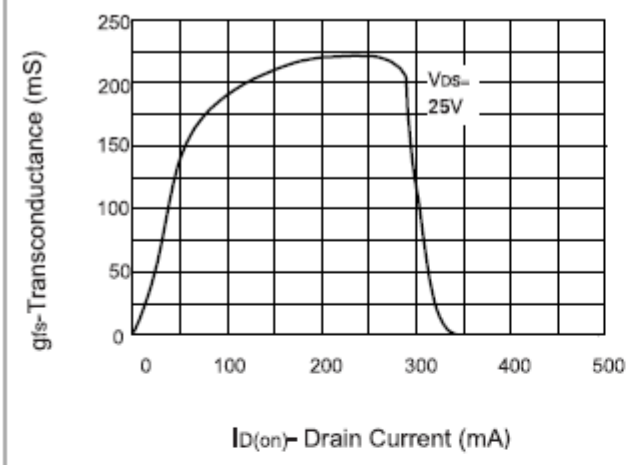
Transfer characteristics



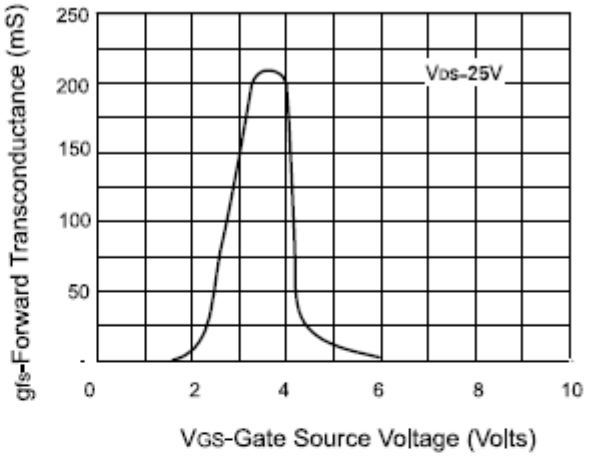
On-resistance vs gate-source voltage



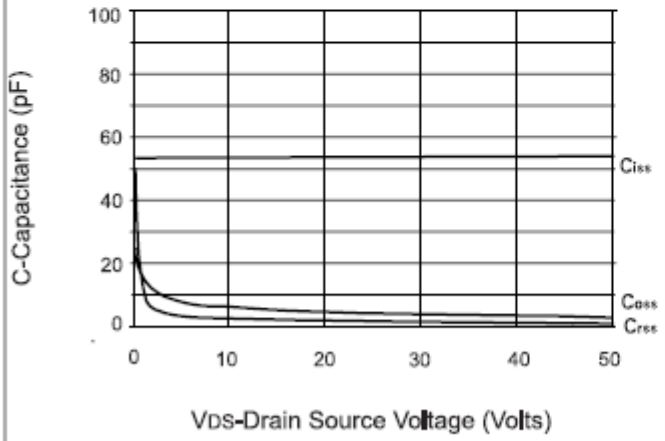
Normalised $R_{DS(on)}$ and $V_{GS(th)}$ temperature



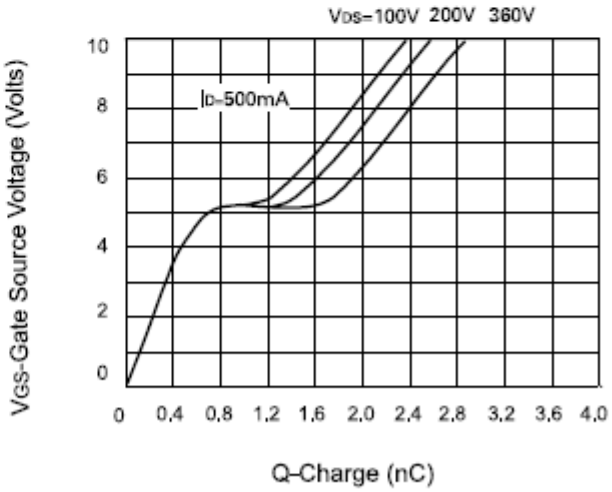
Transconductance v drain current



Transconductance v gate-source voltage



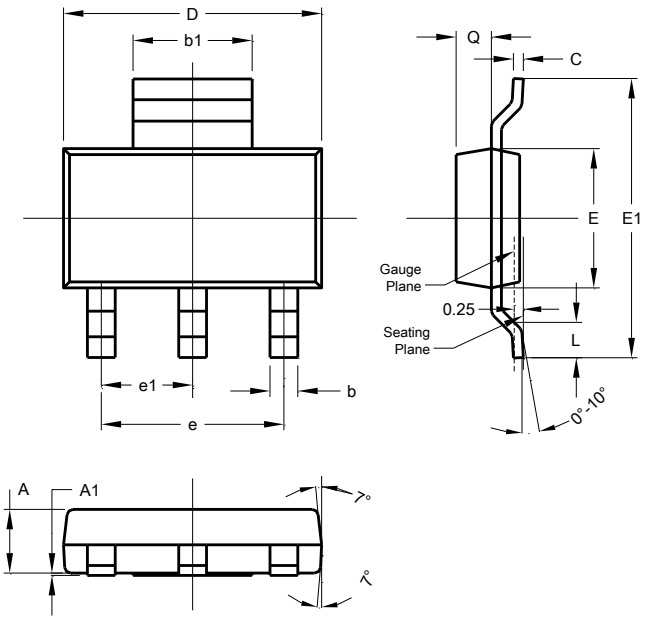
Capacitance v drain-source voltage



Gate charge v gate-source voltage

Package Outline Dimensions

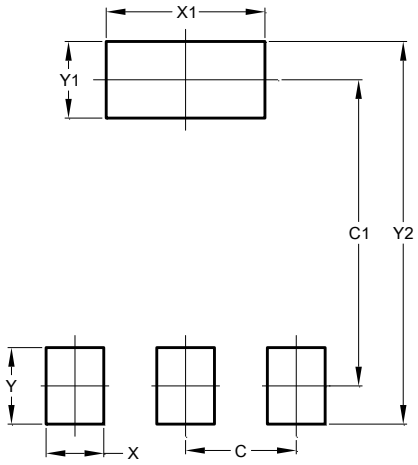
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT223			
Dim	**Min**	**Max**	**Typ**
A	1.55	1.65	1.60
A1	0.010	0.15	0.05
b	0.60	0.80	0.70
b1	2.90	3.10	3.00
C	0.20	0.30	0.25
D	6.45	6.55	6.50
E	3.45	3.55	3.50
E1	6.90	7.10	7.00
e	-	-	4.60
e1	-	-	2.30
L	0.85	1.05	0.95
Q	0.84	0.94	0.89
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
C	2.30
C1	6.40
X	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00

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